PRODUCT SPECIFICATIONS

SHARP®

Integrated Circuits Group

LH52256CH-85LL

256K SRAM

(Model No.: LH525CL2)

Spec No.: EL095124

Issue Date: June 3, 1997

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● When using the products covered herein, please observe the conditions written herein and the precautions outlined in the following paragraphs. In no event shall the company be liable for any damages resulting from failure to strictly adhere to these conditions and precautions.

(1) The products covered herein are designed and manufactured for the following application areas. When using the products covered herein for the equipment listed in Paragraph (2), even for the following application areas, be sure to observe the precautions given in Paragraph (2). Never use the products for the equipment listed in Paragraph (3).

- Office electronics
- Instrumentation and measuring equipment
- Machine tools
- Audiovisual equipment
- Home appliances
- Communication equipment other than for trunk lines

(2) Those contemplating using the products covered herein for the following equipment which demands high reliability, should first contact a sales representative of the company and then accept responsibility for incorporating into the design fail-sale operation, redundancy, and other appropriate measures for ensuring reliability and safety of the equipment and the overall system.

- Control and safety devices for airplanes, trains, automobiles, and other transportation equipment
- Mainframe computers
- Traffic control systems
- Gas leak detectors and automatic cutoff devices
- Rescue and security equipment
- Other safety devices and safety equipment, etc.

(3) Do not use the products covered herein for the following equipment which demands extremely high performance in terms of functionality, reliability, or accuracy.

- Aerospace equipment
- Communications equipment for trunk lines
- Control equipment for the nuclear power industry
- Medical equipment related to life support, etc.

(4) Please direct all queries and comments regarding the interpretation of the above three Paragraphs to a sales representative of the company.

● Please direct all queries regarding the products covered herein to a sales representative of the company.

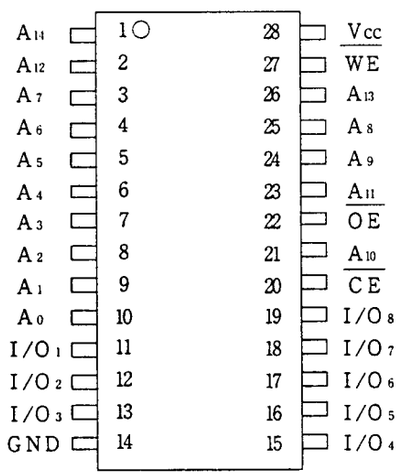
1. Description

The LH52256CH-85LL is a static RAM organized as 32,768×8 bit with provides low-power standby mode.
It is fabricated using silicon-gate CMOS process technology.

Features

○Access Time ・・・・ 85 ns (Max.)
○Operating current ・・・・ 40 mA (Max.)
・・・・ 10 mA (Max. t_{RC}, t_{WC}=1 μs)
○Standby current ・・・・ 40 μA (Max.)
○Data retention current ・・・・ 1.0 μA (Max. V_{CCDR}=3V, Ta=25℃)
○Wide operating voltage range ・・・・ 4.5V to 5.5V
○Operating temperature ・・・・ −40℃ to +85℃
○Fully static operation
○Three-state output
○Not designed or rated as radiation hardened
○28 pin DIP (DIP28-P-600) plastic package
○N-type bulk silicon

2. Pin Configuration



(Top View)

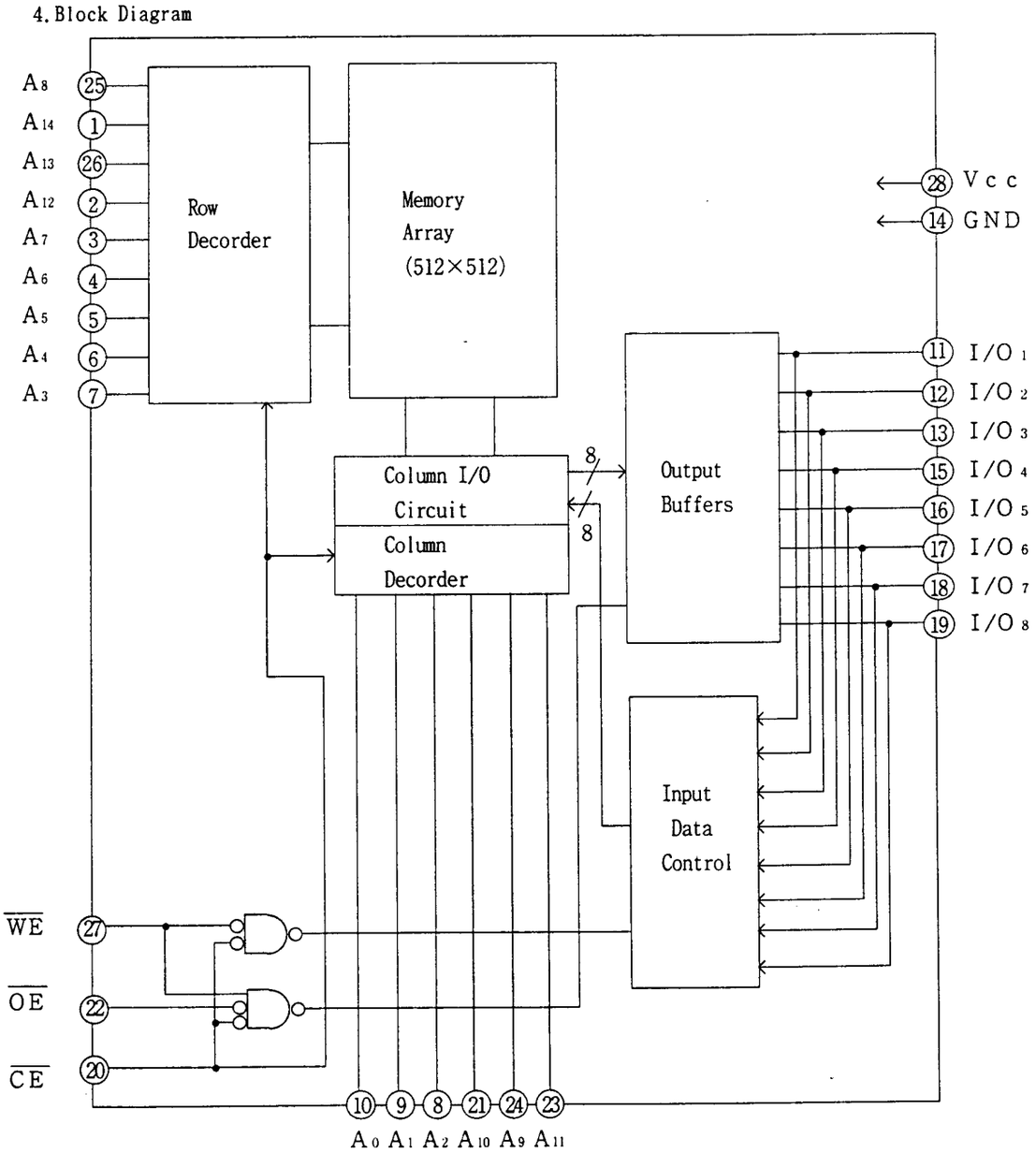
Pin Name	Function
A_0 to A_{14}	Address inputs
$\overline{CE}$	Chip enable
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
I/O_1 to I/O_8	Data inputs/outputs
V_{CC}	Power supply
GND	Ground

3. Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O_1 to I/O_8	Supply current
H	*	*	Standby	High impedance	Standby (I_{SB})
L	H	L	Read	Data output	Active (I_{CC})
L	H	H	Output disable	High impedance	Active (I_{CC})
L	L	*	Write	Data Input	Active (I_{CC})

(*=Don't Care, L=Low, H=High)

4. Block Diagram



5. Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Supply voltage (*1)	V_{CC}	−0.5 to +7.0	V
Input voltage (*1)	V_{IN}	−0.5 (*2) to V_{CC}+0.5	V
Operating temperature	T_{opr}	−40 to +85	℃
Storage temperature	T_{stg}	−65 to +150	℃

Note) *1. The maximum applicable voltage on any pin with respect to GND.
*2. Undershoot of −3.0V is allowed width of pluse bellow 50ns.

6. Recommended DC Operating Conditions

(Ta= −40℃ to +85℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage	V_{IH}	2.2		V_{CC}+0.5	V
	V_{IL}	−0.5 (*3)		0.8	V

Note) *3. Undershoot of −3.0V is allowed width of pluse below 50ns.

7. DC Electrical Characteristics

(Ta=−40℃ to +85℃, Vcc= 4.5V to 5.5V)

Parameter	Symbol	Conditions	Min.	Typ. (*4)	Max.	Unit
Input leakage current	I_{LI}	V_{IN}=0V to V_{CC}	−1.0		1.0	μA
Output leakage current	I_{LO}	$\overline{CE}$=V_{IH} or $\overline{OE}$=V_{IH} $V_{I/O}$=0V to V_{CC}	−1.0		1.0	μA
Operating supply current	I_{CC}	Minimum cycle V_{IN}=V_{IL} or V_{IH}, $I_{I/O}$=0mA, $\overline{CE}$=V_{IL}		25	40	mA
	I_{CC1}	t_{RC}, t_{WC}=1μs V_{IN}=V_{IL} or V_{IH}, $I_{I/O}$=0mA, $\overline{CE}$=V_{IL}			10	mA
Standby current	I_{SB}	$\overline{CE}$ ≧V_{CC}−0.2V		0.6	40	μA
	I_{SB1}	$\overline{CE}$=V_{IH}			3	mA
Output voltage	V_{OL}	I_{OL}= 2.1mA			0.4	V
	V_{OH}	I_{OH}=−1.0mA	2.4			V

Note) *4. Typical values at Vcc=5.0V, Ta=25℃.

8. AC Electrical Characteristics

AC Test Conditions

Input pulse level	0.6V to 2.4V
Input rise and fall time	10ns
Input and Output timing Ref. level	1.5V
Output load	1TTL+C_L (100pF) (*5)

Note) *5. Including scope and jig capacitance.

Read cycle

(Ta=−40℃ to +85℃, Vcc= 4.5V to 5.5V)

Parameter	Symbol	Min.	Max.	Unit	
Read cycle time	t_{RC}	85		ns	
Address access time	t_{AA}		85	ns	
$\overline{CE}$ access time	t_{ACE}		85	ns	
Output enable to output valid	t_{OE}		35	ns	
Output hold from address change	t_{OH}	10		ns	
$\overline{CE}$ Low to output active	t_{LZ}	10		ns	*6
$\overline{OE}$ Low to output active	t_{OLZ}	5		ns	*6
$\overline{CE}$ High to output in High impedance	t_{HZ}	0	30	ns	*6
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0	30	ns	*6

Write cycle

(Ta=−40℃ to +85℃, Vcc= 4.5V to 5.5V)

Parameter	Symbol	Min.	Max.	Unit	
Write cycle time	t_{WC}	85		ns	
$\overline{CE}$ Low to end of write	t_{CW}	55		ns	
Address valid to end of write	t_{AW}	55		ns	
Address setup time	t_{AS}	0		ns	
Write pluse width	t_{WP}	40		ns	
Write recovery time	t_{WR}	0		ns	
Input data setup time	t_{DW}	30		ns	
Input data hold time	t_{DH}	0		ns	
$\overline{WE}$ High to output active	t_{OW}	5		ns	*6
$\overline{WE}$ Low to output in High impedance	t_{WZ}	0	30	ns	*6
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0	30	ns	*6

Note) *6. Active output to High impedance and High impedance to output active tests specified for a ±200mV transition from steady state levels into the test load.

9. Data Retention Characteristics

(Ta=−40℃ to +85℃)

Paramenter	Symbol	Conditions		Min.	Typ. (*7)	Max.	Unit
Data Retention supply voltage	V_{CCDR}	$\overline{CE} \geqq V_{CCDR}-0.2V$		2.0		5.5	V
Data Retention supply current	I_{CCDR}	$V_{CCDR}=3V$	Ta=25℃		0.3	1.0	μA
			Ta=70℃			15	μA
		$\overline{CE} \geqq V_{CCDR}-0.2V$ (*5)				20	μA
Chip enable setup time	t_{CDR}			0			ns
Chip enable hold time	t_R			(*8) t_{RC}			ns

Note) * 7. Typical values at Ta=25℃

* 8. Read Cycle

10. Pin Capacitance

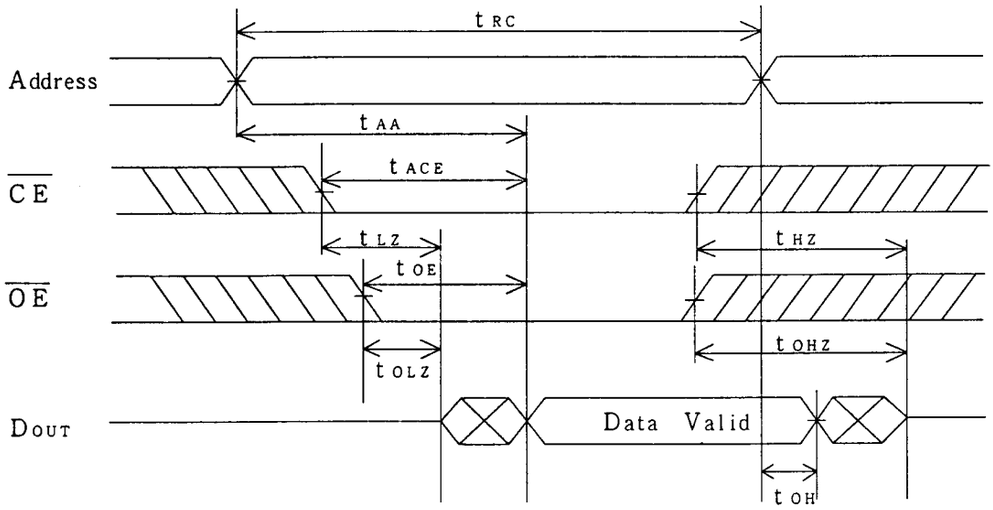
(Ta=25℃, f=1MHz)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Input capacitance	C_{IN}	$V_{IN}=0V$			7	pF	* 9
I/0 capacitance	$C_{I/O}$	$V_{I/O}=0V$			10	pF	* 9

Note) * 9. This parameter is sampled and not production tested.

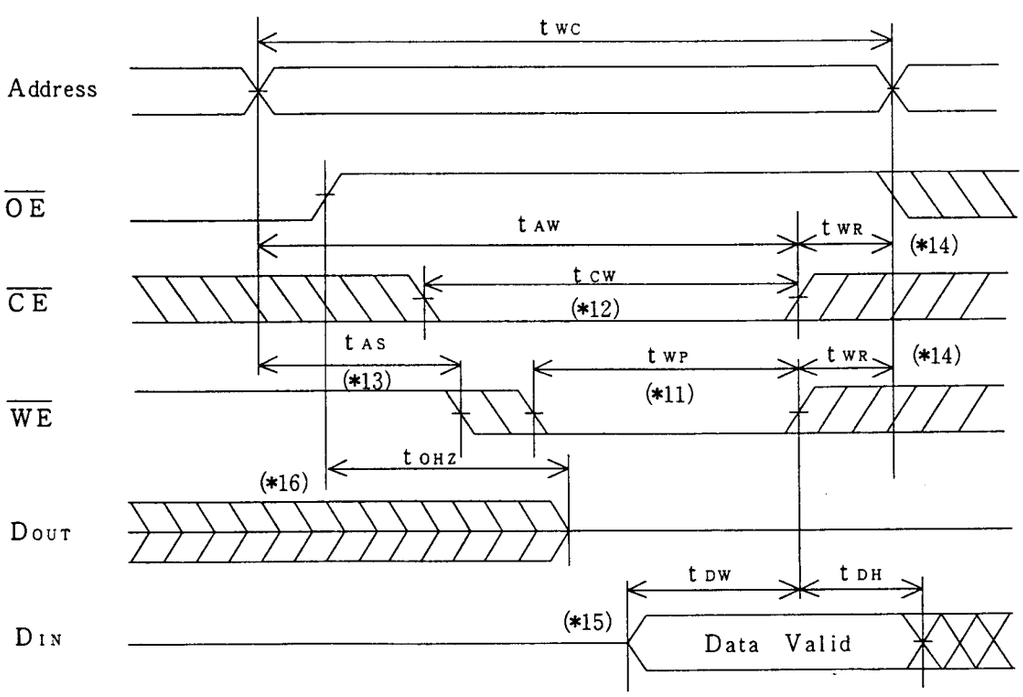
11. Timing Chart

Read cycle timing chart— (*10)

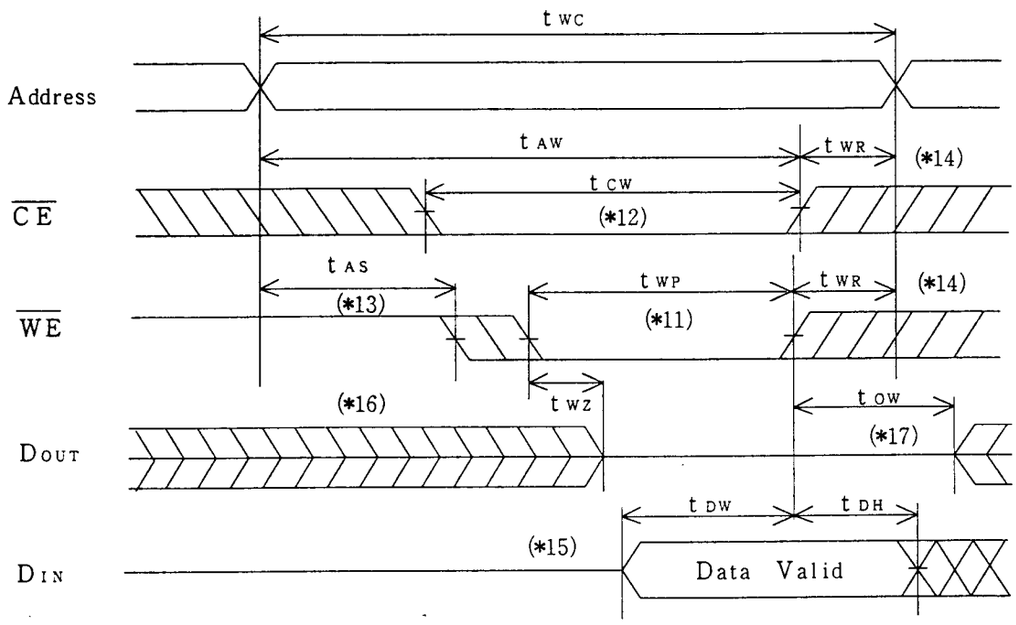


Note) *10. $\overline{WE}$ is high for Read cycle.

Write cycle timing chart— ($\overline{OE}$ Controlled)



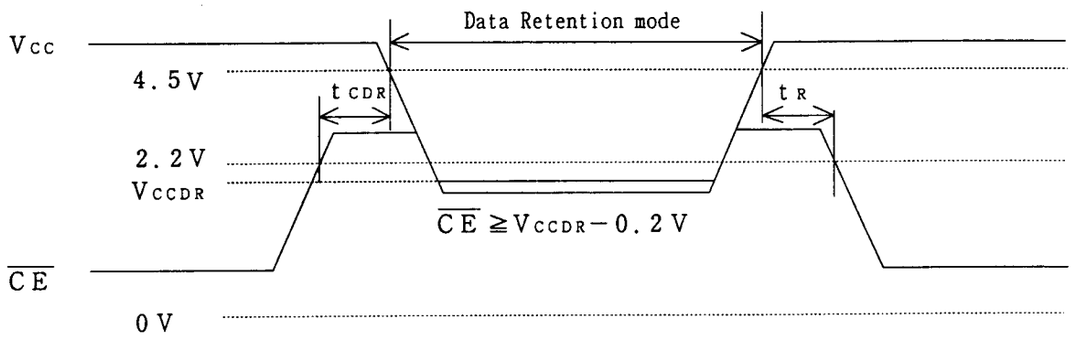
Write cycle timing chart— ($\overline{OE}$ Low fixed)



Note) * 11. A write occurs during the overlap of a low $\overline{CE}$, and a low $\overline{WE}$,
A write begins at the latest transition among $\overline{CE}$ going low, and $\overline{WE}$ going low.
A write ends at the earliest transition among $\overline{CE}$ going high, and $\overline{WE}$ going high.
t_{WP} is measured from the beginning of write to the end of write.

* 12. t_{CW} is measured from the later of $\overline{CE}$ going low to the end of write.
* 13. t_{AS} is measured from the address valid to the beginning of write.
* 14. t_{WR} is measured from the end of write to the address change.
* 15. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
* 16. If $\overline{CE}$ goes low simultaneously with $\overline{WE}$ going low or after $\overline{WE}$ going low, the outputs remain in high impedance state.
* 17. If $\overline{CE}$ goes high simultaneously with $\overline{WE}$ going high or before $\overline{WE}$ going high, the outputs remain in high impedance state.

Data Retention timing chart– $\overline{CE}$ Controlled)



12 Package and packing specification

1. Package Outline Specification

Refer to drawing No.AA852

2. Markings

2－1. Marking contents

(1) Product name : LH52256CH－85LL

(2) Company name : SHARP

(3) Date code

(Example) YY WW ××× Indicates the product was manufactured in the WWth week of 19YY.

→ Denotes the production ref.code (1~3)

→ Denotes the production week. (01,02,03,・・・・・52,53)

→ Denotes the production year. (Lower two digits of the year.)

(4) The marking of "JAPAN" indicates the country of origin.

2－2. Marking layout

Refer to drawing No.AA852

(This layout does not define the dimensions of marking character and marking position.)

3. Packing Specification

3－1. Packing materials

Material Name	Material Specification	Purpose
Magazine	Anti-static treated plastic (15devices/magazine)	Packing of device
Stopper	Plastic or rubber	Fixing of device
Label	Paper	Indication of product name, quantity and date of manufacture.
Inner case	Cardboard (600devices/cace)	Fixing of magazine
Outer case	Cardboard	Outer packing of magazine

(Devices shall be inserted into a magazine (sleeve) in the same direction.)

3－2. Outline dimension of magazine (sleeve)

Refer to attached drawing

4. Precaution For Unpacking

(1) Unpacking should be done on the stand as well as human body treated with anti-ESD.

(2) Anti-ESD treatment is given to a magazine. Use the equivalent magazine , if it is changed to another one.

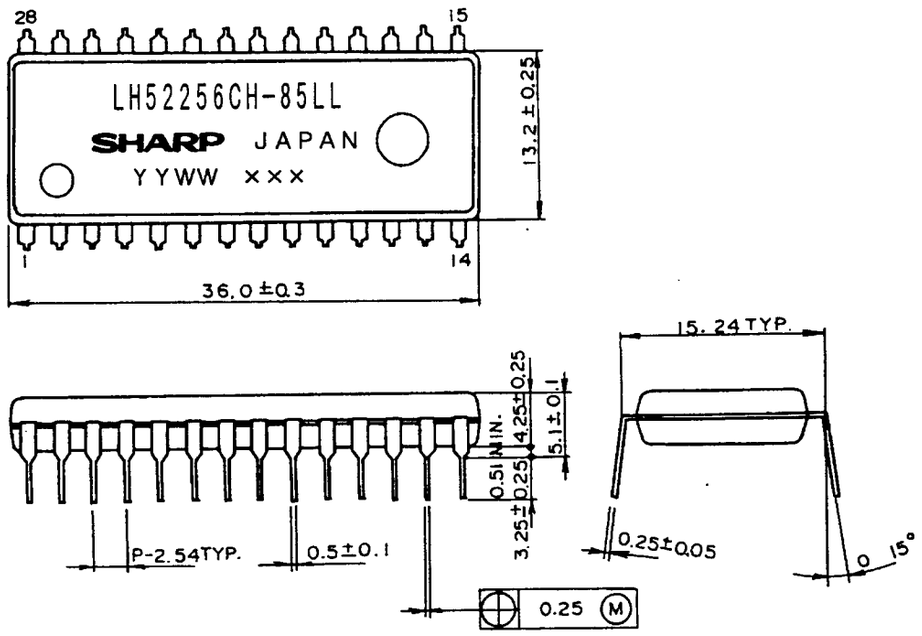
(3) Be sure to fix two stoppers to both ends of a magazine when storage to prevent the devices from slipping.

5. Surface Mount Conditions

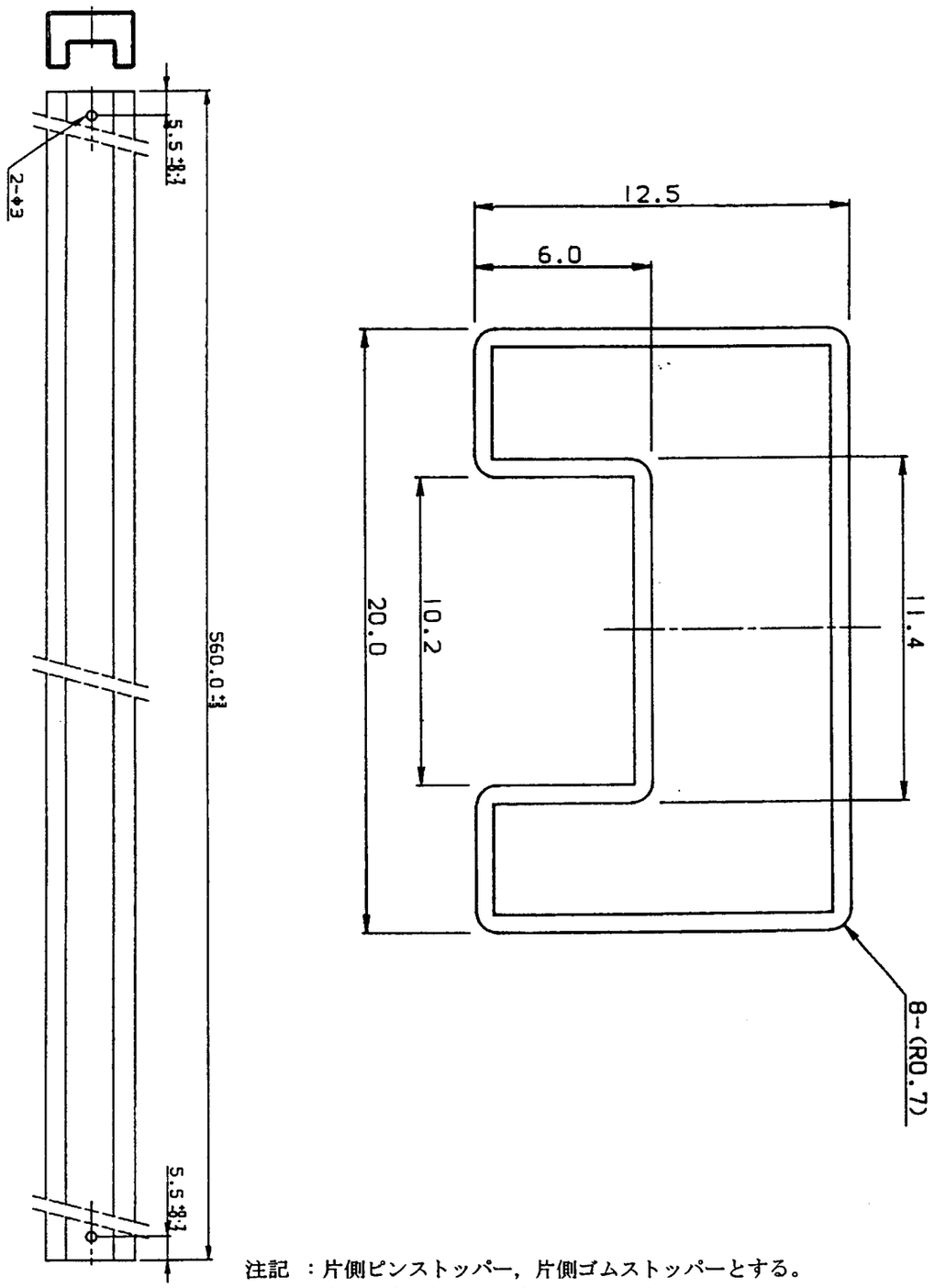
Please perform the following conditions when mounting ICs not to deteriorate IC quality.

5－1.Soldering conditions(The following conditions are valid only for one time soldering.)

Mounting Method	Temperature and Duration	Measurement Point
Solder dipping	245℃ or less, duration of less than 3 seconds/dip, total of 5 seconds. (Only the appropriate parts of leads for soldering are immersed in the surface of a jet stream solder bath. During soldering, the solder stream must not come into direct contact with the plastic body of package.)	Solder bath.
Manual soldering (soldering iron)	260℃ or less, duration of less than 10 seconds. (Only the appropriate parts of leads for soldering are soldered with a soldering iron. During soldering, the soldering iron must not come into direct contact with the plastic body of package.)	IC outer lead surface.



名称 NAME	DIP28-P-600	リード仕上 LEAD FINISH	TIN-LEAD PLATING	備考 NOTE プラスチックパッケージ外形寸法は、バリを含まないものとする。 Plastic body dimensions do not include burr of resin.
DRAWING NO.	AA852	単位 UNIT	mm	



注記 ：片側ピンストッパー，片側ゴムストッパーとする。
指示無き寸法公差は全て±０．４とする。

NOTES : One end of magazine (sleeve) is plugged by stopper which is made of rubber, and another end of magazine (sleeve) is plugged by plastic pin-stopper.
All tolerances are ±0.4mm unless otherwise specified

名称 NAME	DP600SPK−A2			備考 NOTE
DRAWING NO.	CV651	単位 UNIT	mm	

Static SRAM RAM Random Access Memory LH52256CH-85LL 256K (32Kx8) (85 ns) (DIP)

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